

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original)                      A dielectric ceramic composition including at least  
    a main component containing a dielectric oxide having a composition expressed by  
 $[(Ca_xSr_{1-x})O]_m[(Ti_yZr_{1-y-z}Hf_z)O_2]$ ,  
    a first subcomponent containing a Mn oxide and/or an Al oxide, and  
    a glass component:

   wherein “m”, “x”, “y” and “z” indicating composition mole ratios in the formula  
 included in said main component are in relationships of

$$0.90 \leq m \leq 1.04$$

$$0.5 \leq x < 1$$

$$0.01 \leq y \leq 0.10$$

$$0 < z \leq 0.20.$$

2. (Original)                      The dielectric ceramic composition as set forth in claim 1,  
 including 0.2 to 5 mol% of said Mn oxide in terms of MnO and 0.1 to 10 mol% of said Al  
 oxide in terms of Al<sub>2</sub>O<sub>3</sub> with respect to 100 mol% of said main component.

3. (Currently Amended)              The dielectric ceramic composition as set forth in claim 1-~~or 2~~,  
 including 0 to 2.5 mol% (note that 0 is excluded) of a V oxide in terms of V<sub>2</sub>O<sub>5</sub> with respect  
 to 100 mol% of said main component.

4. (Currently Amended)              The dielectric ceramic composition as set forth in ~~any one of~~  
~~claims 1 to 3~~claim 1, wherein said glass component contains at least SiO<sub>2</sub> as a main  
 component.

5. (Currently Amended)              The dielectric ceramic composition as set forth in ~~any one of~~  
~~claims 1 to 4~~claim 1, wherein said glass component is expressed by  $[(Ba_vCa_{1-v})O]_wSiO_2$ , “v”  
 and “w” in the composition formula of said glass component are in ranges of  $0 \leq v \leq 1$  and

$0.5 \leq w \leq 4.0$ , and said glass component is included by 0.5 to 15 mol% with respect to 100 mol% of said main component.

6. (Currently Amended) The dielectric ceramic composition as set forth in ~~any one of claims 1 to 5~~claim 1, including at least one of rare earth elements including Sc and Y by 0.02 to 1.5 mol% with respect to 100 mol% of said main component.

7. (Currently Amended) The dielectric ceramic composition as set forth in ~~any one of claims 1 to 6~~claim 1, including at least one of Nb, Mo, Ta, W and Mg by 0.02 to 1.5 mol% with respect to 100 mol% of said main component.

8. (Currently Amended) The dielectric ceramic composition as set forth in ~~any one of claims 1 to 7~~claim 1, wherein "m" indicating a composition mole ratio in the formula contained in said main component is  $1.005 \leq m \leq 1.025$ .

9. (Currently Amended) A production method of the dielectric ceramic composition as set forth in ~~any one of claims 1 to 8~~claim 1, comprising the steps of:

preparing materials of said dielectric ceramic composition;  
mixing said materials;  
obtaining a calcinated substance by collectively calcinating said mixed materials to bring solid-phase reaction by using a dry synthesis method; and  
obtaining said dielectric ceramic composition by performing main firing on said calcinated substance.

10. (Currently Amended) An electronic device having a dielectric layer:

wherein said dielectric layer is composed of the dielectric ceramic composition as set forth in ~~any one of claims 1 to 8~~claim 1.

11. (Currently Amended) An electronic device having alternately stacked internal electrodes and dielectric layers, wherein said dielectric layers are composed of the dielectric ceramic composition as set forth in ~~any one of claims 1 to 8~~claim 1.

12. (Original)                      The electronic device as set forth in claim 11, wherein said internal electrode includes at least nickel.

13. (Currently Amended)        The electronic device as set forth in claim 11 ~~or 12~~, wherein an average particle diameter of a crystal in said dielectric layer is 2  $\mu\text{m}$  or less.

14. (Currently Amended)        A production method of the electronic device as set forth in ~~any one of claims 11 to 13~~claim 11, wherein main firing at 1300°C or lower is performed on said internal electrodes and dielectric layers at a time.